

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently Amended) A method for removing a resist pattern, comprising:
forming a metal film over a substrate;
forming a resist pattern of a positive resist composition containing a photosensitizer over
the metal film;
etching the metal film by using the resist pattern;
irradiating the resist pattern with a light having a photosensitive wavelength region of the
photosensitizer after etching the metal film; ~~forming said resist pattern;~~ and
removing the resist pattern by using a resist stripper.

2. (Currently Amended) A method for removing a resist pattern ~~manufacturing a~~
~~semiconductor device~~, comprising:
forming a metal film over a substrate;
forming a resist pattern of a positive resist composition containing a photosensitizer over
the metal film; ~~on a material to be processed;~~
~~irradiating the resist pattern with a light having a photosensitive wavelength region of the~~
~~photosensitizer after forming said resist pattern;~~
etching the metal film ~~performing an etching process on the material to be processed by~~
using the resist pattern; ~~as a mask after irradiating the resist pattern with the light;~~
removing the resist pattern by using a resist stripper;
irradiating an unprocessed portion of the resist pattern with a light having a
photosensitive wavelength region of the photosensitizer after removing the resist pattern; and
treating the unprocessed portion of the resist pattern by using a developer.

~~performing a resist removing process on the resist pattern; and
thereby forming said semiconductor device.~~

3. (Currently Amended) A method for manufacturing a semiconductor device,
comprising:

forming a metal film over a substrate;

forming a resist pattern of a positive resist composition containing a photosensitizer over
the metal film; ~~on a material to be processed;~~

etching the metal film ~~performing an etching process on the material to be processed by~~
using the resist pattern; ~~as a mask, after forming said resist pattern;~~

irradiating the resist pattern with a light having a photosensitive wavelength region of the
photosensitizer after etching the metal film; ~~performing the etching process on the material to be~~
~~processed; and~~

~~performing a resist removing process on the resist pattern; and
thereby forming said semiconductor device.~~

4. (Currently Amended) A method for manufacturing a semiconductor device,
comprising:

forming a metal film over a substrate;

forming a resist pattern of a positive resist composition containing a photosensitizer over
the metal film; ~~on a material to be processed;~~

etching the metal film ~~performing an etching process on the material to be processed by~~
using the resist pattern; ~~as a mask, after forming said resist pattern;~~

removing the resist pattern by using a resist stripper;

~~performing a resist removing process on the resist pattern;~~

irradiating an unprocessed portion of the resist pattern with a light having a
photosensitive wavelength region of the photosensitizer after removing the resist pattern; and

treating ~~[[an]]~~ the unprocessed portion of the ~~positive~~ resist pattern by using a developer after irradiating the resist pattern with the light having the photosensitive wavelength region of the photosensitizer; ~~and~~
thereby forming said semiconductor device.

5. (Currently Amended) A method for removing a resist pattern ~~manufacturing a semiconductor device~~ according to claim 1,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type~~[[;]]~~, and
wherein the photosensitizer is diazonaphthoquinone (DNQ).

6. (Currently Amended) A method for removing a resist pattern ~~manufacturing a semiconductor device~~ according to claim 2,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type~~[[;]]~~, and
wherein the photosensitizer is diazonaphthoquinone (DNQ).

7. (Currently Amended) A method for manufacturing a semiconductor device according to claim 3,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type~~[[;]]~~, and
wherein the photosensitizer is diazonaphthoquinone (DNQ).

8. (Currently Amended) A method for manufacturing a semiconductor device according to claim 4,

wherein the positive resist composition containing the photosensitizer is a diazonaphthoquinone (DNQ)-novolac resin type~~[[;]]~~, and
wherein the photosensitizer is diazonaphthoquinone (DNQ).

9. (Currently Amended) A method for removing a resist pattern ~~manufacturing a semiconductor device~~ according to claim 2,

wherein the ~~material to be processed is a metal film~~ forms to form an electrode of a thin film transistor ~~said semiconductor~~.

10. (Currently Amended) A method for manufacturing a semiconductor device according to claim 3,

wherein the ~~material to be processed is a metal film~~ forms to form an electrode of a thin film transistor ~~said semiconductor~~.

11. (Currently Amended) A method for manufacturing a semiconductor device according to claim 4,

wherein the ~~material to be processed is a metal film~~ forms to form an electrode of a thin film transistor ~~said semiconductor~~.

12. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over an insulating surface;

forming a gate insulating film over the semiconductor film;

forming a first-layer gate electrode film over the gate insulating film;

forming a second-layer gate electrode film over the first-layer gate electrode film;

forming a resist pattern of a positive resist composition containing a photosensitizer, the resist pattern being formed over the second-layer gate electrode film;

~~irradiating the resist pattern with light within a range of photosensitive wavelength of the photosensitizer;~~

performing a first dry etching processing for etching the second-layer gate electrode film to form a second-layer gate electrode;

performing a second dry etching processing for etching the first-layer gate electrode film to form a first-layer gate electrode;

performing a third dry etching processing for etching the first-layer gate electrode and the second-layer gate electrode; [[and]]

irradiating the resist pattern with light within a range of photosensitive wavelengths of the photosensitizer after the first, second and third dry etching processing; and

removing the resist pattern[[:]],

wherein the first-layer gate electrode has a first shape tapered portion and the second-layer gate electrode has a second shape tapered portion after the third dry etching processing; and

wherein the first-layer gate electrode extends beyond the second-layer gate electrode after the third dry etching processing.

13. (Currently Amended) A method for manufacturing a semiconductor device comprising:

forming a semiconductor film over an insulating surface;

forming a gate insulating film over the semiconductor film;

forming a gate electrode film over the gate insulating film;

forming a resist pattern of a positive resist composition containing a photosensitizer over the gate electrode film; on a laminated metal layer;

etching the gate electrode film by using the resist pattern;

irradiating the resist pattern with a light having a photosensitive wavelength region of the photosensitizer after etching the gate electrode film; and

removing the resist pattern by using a resist stripper; ~~and~~

~~thereby forming said semiconductor device.~~

14. (Currently Amended) A method for manufacturing a semiconductor device according to claim 13, further comprising:

forming the gate electrode film ~~said laminated metal layer~~ over an acrylic resin layer.

15. (Currently Amended) A method for manufacturing a semiconductor device according to claim 13,

wherein the gate electrode film ~~said laminated metal layer~~ comprises an aluminum film, a titanium nitride film, and a titanium film.

16. (Currently Amended) A method for manufacturing a semiconductor device according to claim 13, wherein a ~~[[an]]~~ range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.

17. (New) A method for manufacturing a semiconductor device according to claim 3, wherein a range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.

18. (New) A method for manufacturing a semiconductor device according to claim 4, wherein a range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.

19. (New) A method for manufacturing a semiconductor device according to claim 12, wherein a range of an exposure period of time to irradiate the resist pattern with the light having the photosensitive wavelength region of the photosensitizer is from 1 seconds to 30 seconds.